
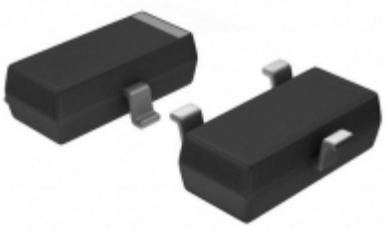
	<p><b>SI2312BDS-T1-E3</b></p>
	<p><b>Hersteller-Teilenummer:</b> SI2312BDS-T1-E3</p> <p><b>Hersteller / Marke:</b> Vishay / Siliconix</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 20V 3.9A SOT23-3</p> <p><b>Datenblätter:</b>  <a href="#">SI2312BDS-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 145678 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

**Spezifikationen**

Teilenummer	SI2312BDS-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 3.9A SOT23-3
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	145678 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	3.9A (Ta)
Rds On (Max) @ Id, Vgs	31 mOhm @ 5A, 4.5V
VGS (th) (Max) @ Id	850mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
















SI2312BDS-T1-E3 ist neu im Original, Suche SI2312BDS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2312BDS-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2312BDS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SI2312BDS</b> VISHAY SI2312BDS VISHAY</p>	 <p><b>SI2312BDS-T1</b> VISHAY VISHAY SOT23</p>	 <p><b>SI2312CDS-T1-E3</b> VISHA SI2312CDS-T1-E3 VISHA</p>	 <p><b>SI2312BDS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 20V 3.9A SOT23-3</p>
 <p><b>SI23120</b> VISHAY SI23120 VISHAY</p>	 <p><b>SI2312BDS-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 20V 3.9A SOT23-3</p>	 <p><b>SI2312/CJ2312</b> Original SOT-23</p>	 <p><b>SI2312BDS-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 20V 3.9A SOT23-3</p>

**heiße Teile**

Mehr

- |  |  |   |  |  |
|--|--|---|--|--|
|  SI2308DS-T1-E3   |  SI2308DS-T1-E3   |  SI2308DS-T1-GE3 |  SI2309BDS-T1-E3  |  SI2309BDS-T1-GE3 |
|  SI2309CDS-T1-GE3 |  SI2309CDS-T1-GE3 |  SI2309DS        |  SI2309DS-T1      |  SI2309DS-T1-E3   |
|  SI2309DS-T1-E3   |  SI2309DS-T1-GE3  |  SI2309DS-TI-E3  |  SI2309DS/A92T    |  SI2310DS         |
|  SI2310DS-T1-E3   |  SI2310DS-T1-GE3  |  SI2311DS        |  SI2311DS-T1      |  SI2311DS-T1-E3   |
|  SI2311DS-T1-E3   |  SI2311DS-T1-GE3  |  SI2311DS-T1-GE3 |  SI2312BDS        |  SI2312BDS-T1-E3  |
|  SI2312BDS-T1-GE3 |  SI2312BDS-T1-GE3 |  SI2312CDS-T1-E3 |  SI2312CDS-T1-GE3 |  SI2312CDS-T1-GE3 |
|  SI2312DS         |  SI2312DS-T1      |  SI2312DS-T1-E3  |  SI2312DS-T1-GE3  |  SI2313DS         |
|  SI2313DS-T1-E3   |  SI2313DS-T1-GE3  |  SI2314DS        |  SI2314DS-T1-E3   |  SI2314DS-T1-GE3  |
|  SI2314EDS        |  SI2314EDS-T1-E3  |  SI2314EDS-T1-E3 |  SI2314EDS-T1-GE3 |  SI2314EDS-T1-GE3 |
|  SI2315BDS        |  SI2315BDS-T1-E3  |  SI2315BDS-T1-E3 |  SI2315BDS-T1-GE3 |  SI2315BDS-T1-GE3 |

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited